TOSHIBA Transistor Silicon PNP Epitaxial Type

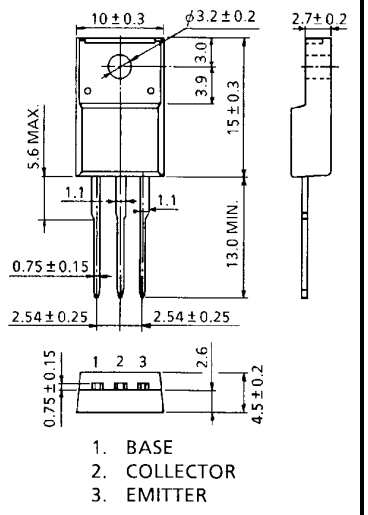
2SA1837

Power Amplifier Applications

Driver Stage Amplifier Applications

- High transition frequency: f_T = 70 MHz (typ.)
- Complementary to 2SC4793

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-10R1A

Weight: 1.7 g (typ.)

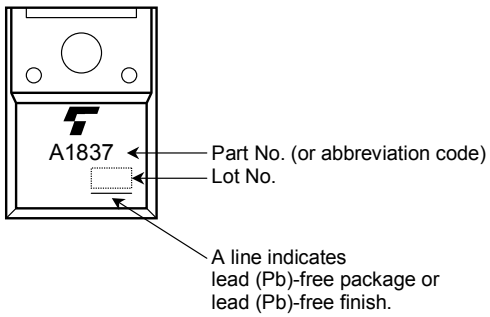
Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	−230	V
Collector-emitter voltage		V_{CEO}	−230	V
Emitter-base voltage		V_{EBO}	−5	V
Collector current		I_C	−1	A
Base current		I_B	−0.1	A
Collector power dissipation	Ta = 25°C	P_C	2.0	W
	Tc = 25°C		20	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

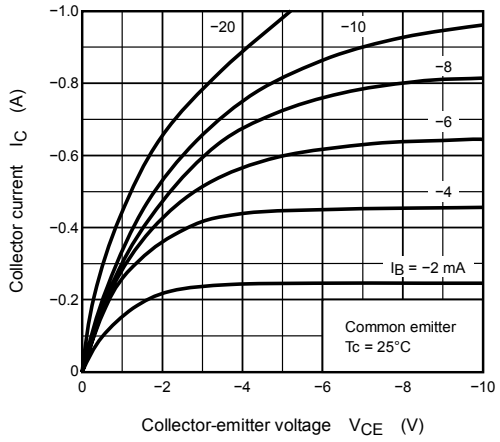
Electrical Characteristics (Tc = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −230 V, I_E = 0	—	—	−1.0	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = −10 mA, I_B = 0	−230	—	—	V
DC current gain	h_{FE}	V_{CE} = −5 V, I_C = −100 mA	100	—	320	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −500 mA, I_B = −50 mA	—	—	−1.5	V
Base-emitter voltage	V_{BE}	V_{CE} = −5 V, I_C = −500 mA	—	—	−1.0	V
Transition frequency	f_T	V_{CE} = −10 V, I_C = −100 mA	—	70	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_C = 0, f = 1 MHz	—	30	—	pF

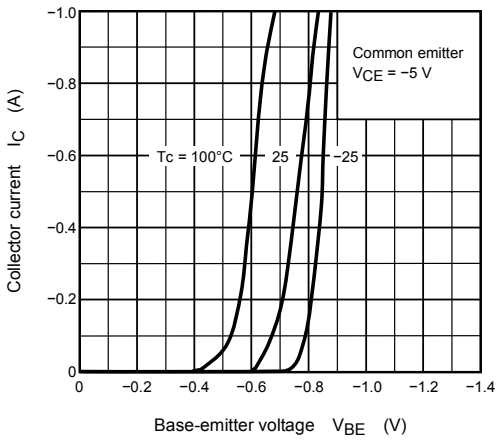
Marking



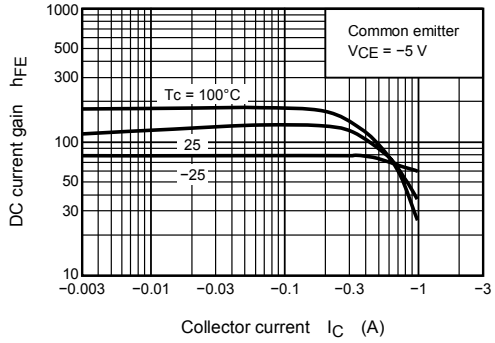
$I_C - V_{CE}$



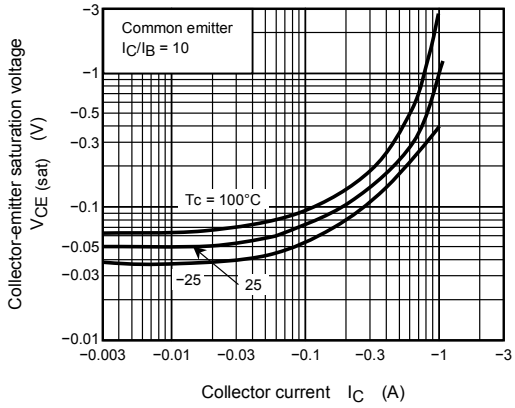
$I_C - V_{BE}$



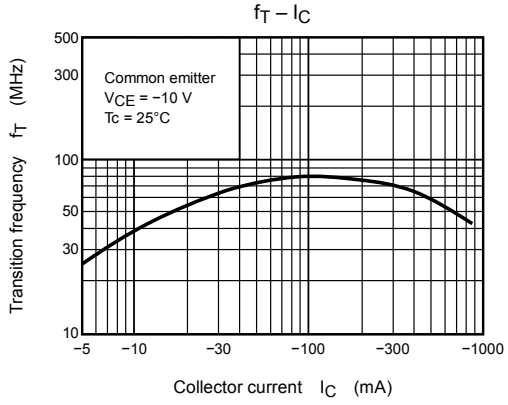
$h_{FE} - I_C$



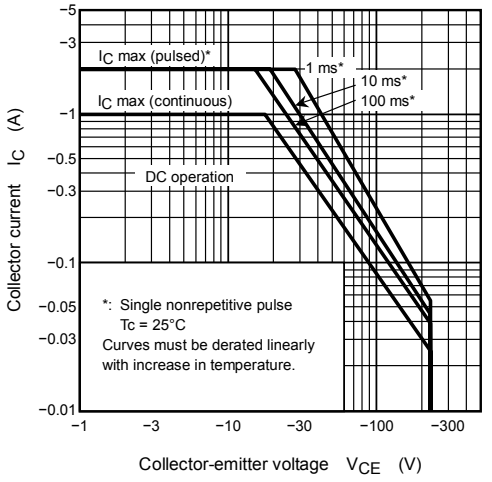
$V_{CE\ (sat)} - I_C$



$f_T - I_C$



Safe Operating Area



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